

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

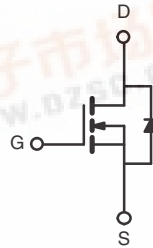
PRODUCT SUMMARY

V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.015
I_D (A)	56
Configuration	Single

TO-263



Top View



N-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified^d
- Characterization Ongoing
- Compliant to RoHS Directive 2002/95/EC
- Find out more about Vishay's Automotive Grade Product Requirements at: www.vishay.com/applications



RoHS
COMPLIANT
HALOGEN
FREE

ORDERING INFORMATION

Package	TO-263
Lead (Pb)-free and Halogen-free	SQM60N06-15-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C = 25$ °C	56
		$T_C = 125$ °C	32
Continuous Source Current (Diode Conduction) ^a	I_S	60	A
Pulsed Drain Current ^b	I_{DM}	227	A
Single Pulse Avalanche Current	I_{AS}	29	A
Single Pulse Avalanche Energy	E_{AS}	42	mJ
Maximum Power Dissipation ^b	P_D	$T_C = 25$ °C	107
		$T_C = 125$ °C	35
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	1.4	°C/W

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.



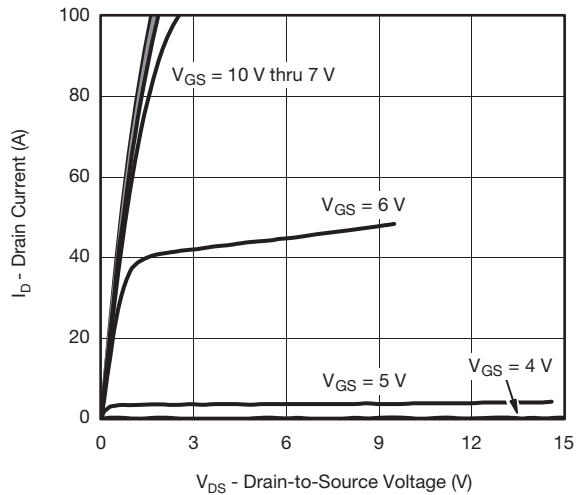
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.5	-	3.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V	-	-	1.0	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	75	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A	-	0.012	0.015	Ω
		V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.027	
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.033	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 30 A		-	61	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	1983	2480	pF
Output Capacitance	C _{Oss}			-	314	395	
Reverse Transfer Capacitance	C _{rss}			-	125	160	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 30 V, I _D = 60 A	-	33	50	nC
Gate-Source Charge ^c	Q _{gs}			-	8.9	-	
Gate-Drain Charge ^c	Q _{gd}			-	7.4	-	
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 0.5 Ω I _D ≅ 60 A, V _{GEN} = 10 V, R _g = 1 Ω		-	11	17	ns
Rise Time ^c	t _r			-	12	18	
Turn-Off Delay Time ^c	t _{d(off)}			-	21	32	
Fall Time ^c	t _f			-	7	11	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	227	A
Forward Voltage	V _{SD}	I _F = 30 A, V _{GS} = 0 V		-	0.9	1.5	V

Notes

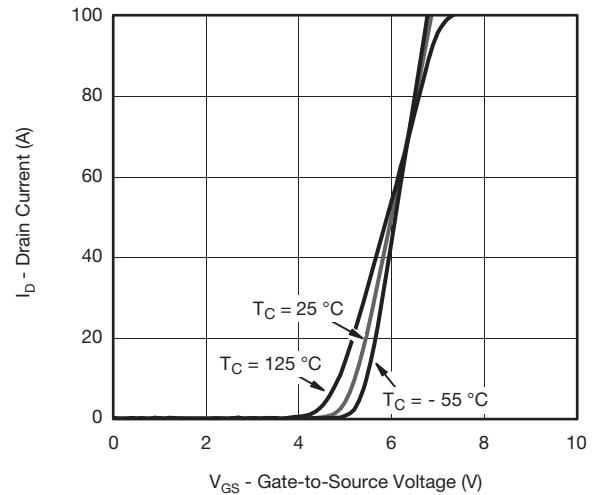
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

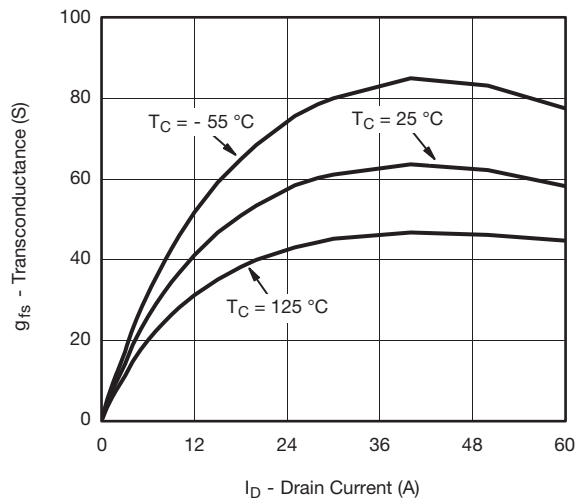
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



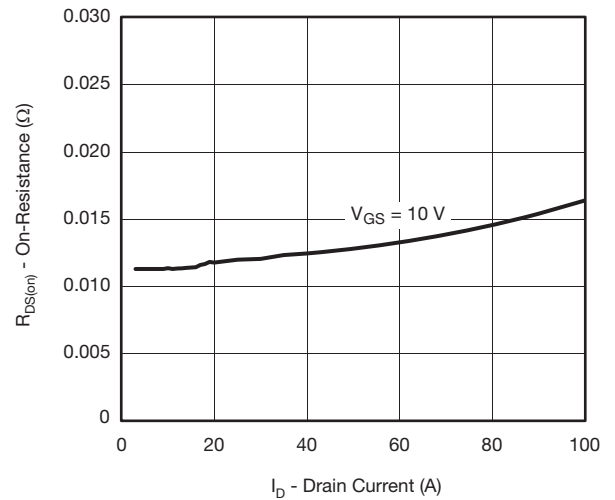
Output Characteristics



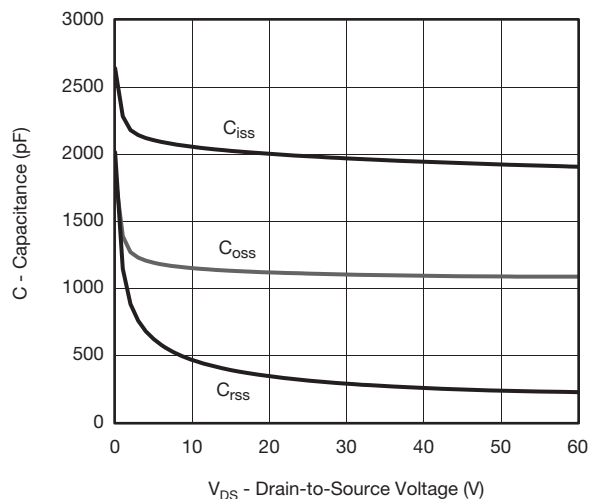
Transfer Characteristics



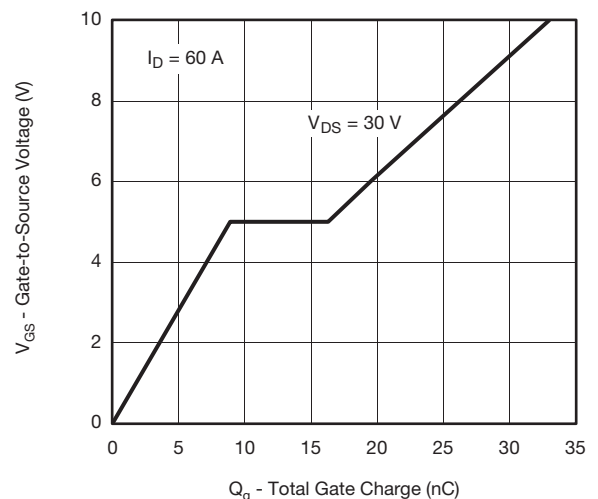
Transconductance



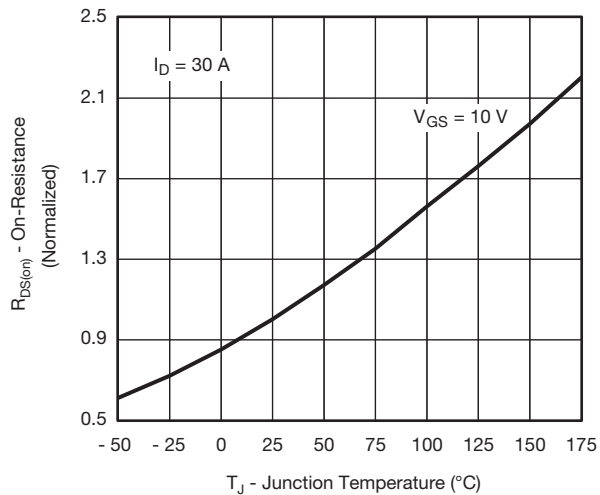
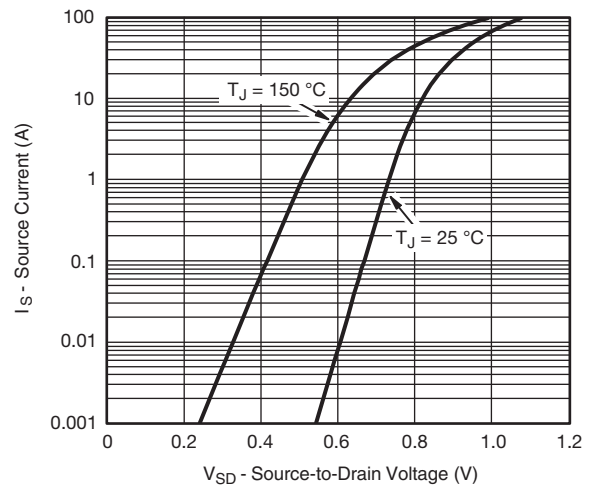
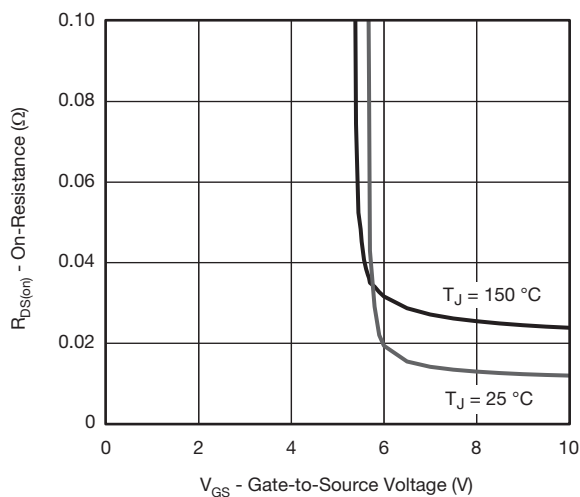
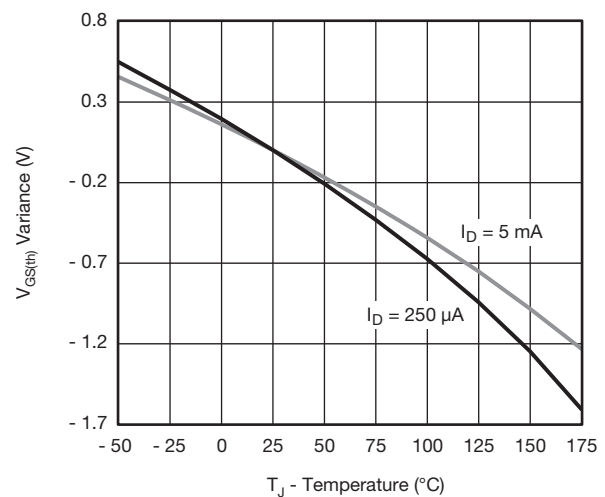
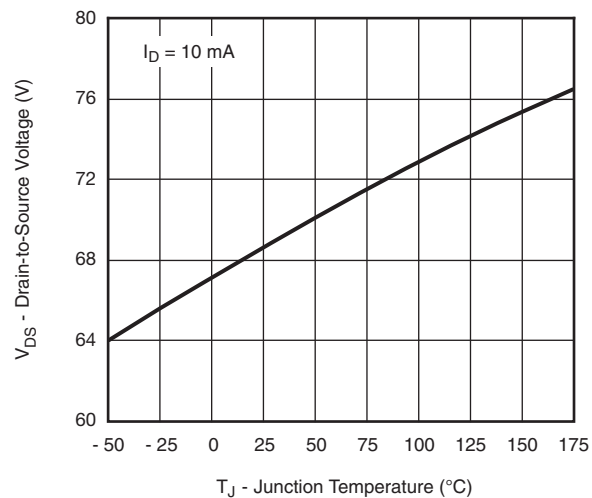
On-Resistance vs. Drain Current



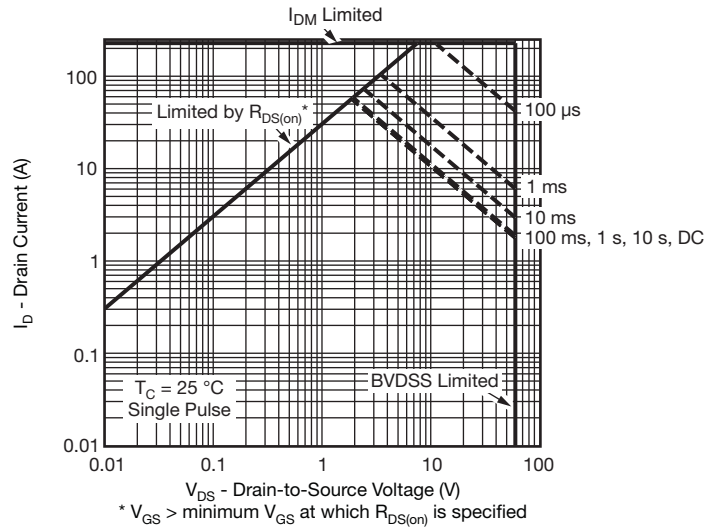
Capacitance



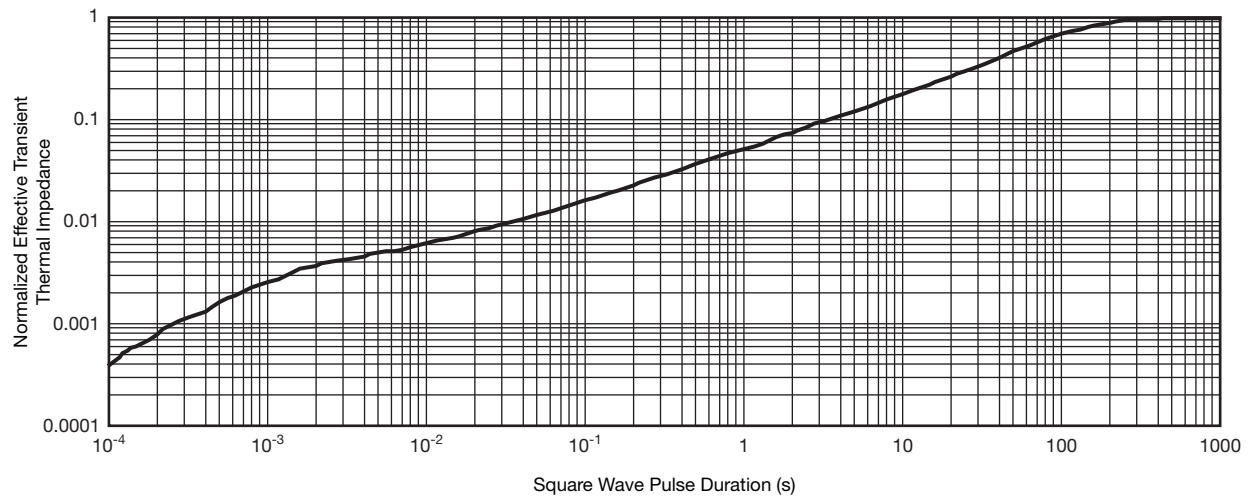
Gate Charge

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)**On-Resistance vs. Junction Temperature****Source Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Drain Source Breakdown vs. Junction Temperature**

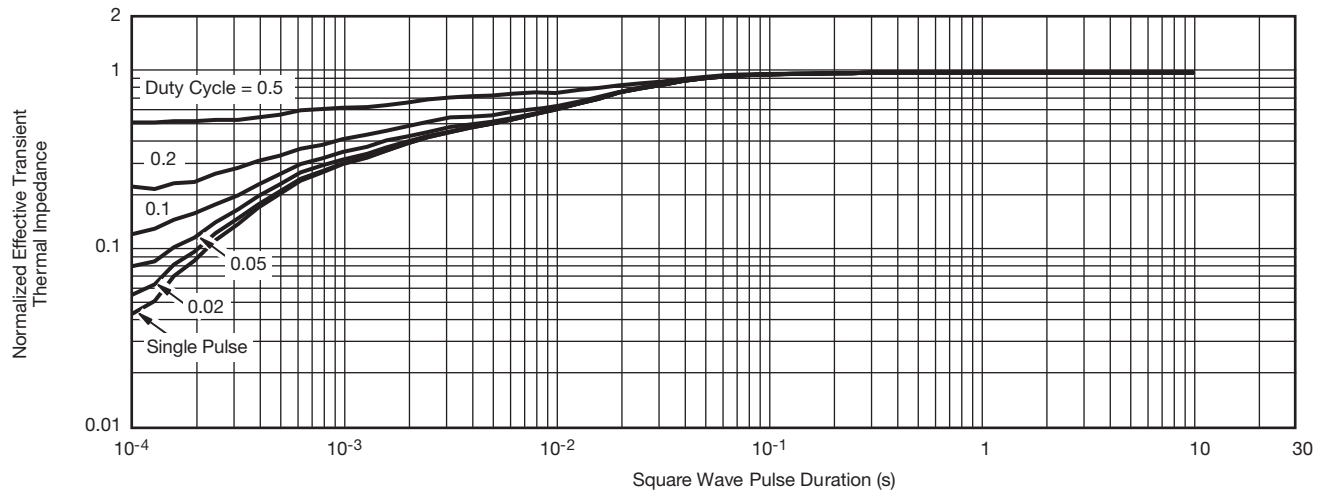
THERMAL RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Case****Note**

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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